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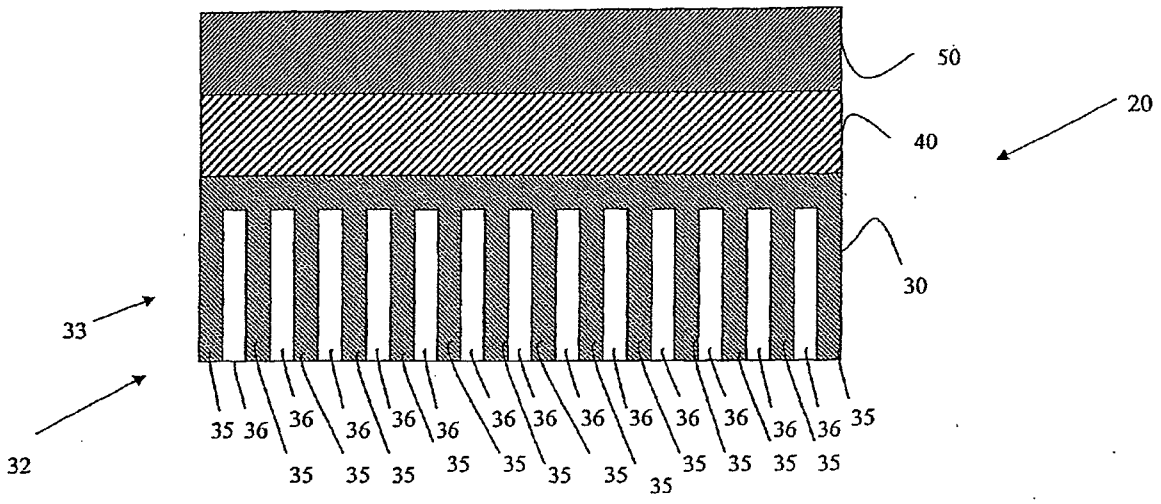
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(54) Title: STRAINED SEMICONDUCTOR SUBSTRATE AND PROCESSES THEREFOR



(57) Abstract: A method of manufacturing an integrated circuit (IC) utilizes a strained silicon (SMOS) substrate (20). The substrate (20) utilizes trenches (36) in a base layer to induce stress in a layer. The substrate can include silicon. The trenches (36) define pillars (35) on a back side of a bulk substrate or base layer of a semiconductor-on-insulator (SOI) wafer.

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